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- (81) 指定国(除另有指明, 要求每一种可提供的国家保护): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN,

(54) Title: DEVICE AND METHOD FOR CLEANING WAFER

(54) 发明名称: 一种用于清洗晶圆的装置和方法

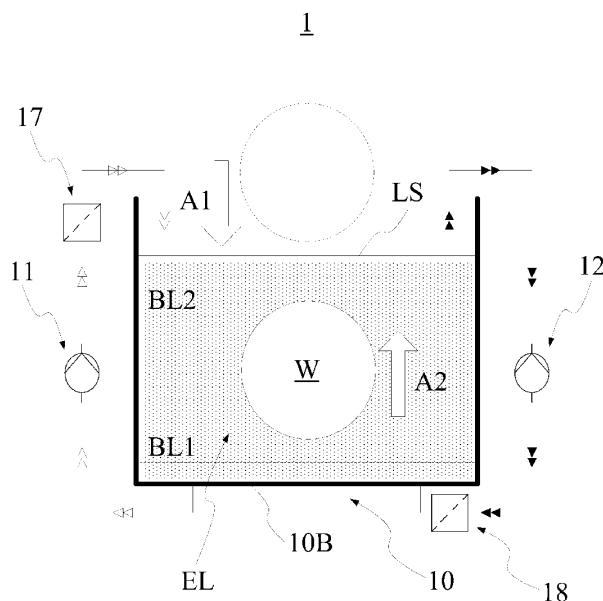


图 1

(57) Abstract: Disclosed in the embodiments of the present application are a device and method for cleaning a wafer. The device may comprise: a cleaning tank body; a first pump, the first pump being used for pumping, during a process of immersing a wafer in an etching liquid accommodated in the cleaning tank body, the etching liquid at the bottom of the cleaning tank body to a liquid level of the etching liquid accommodated in the cleaning tank body via the outside of the cleaning tank body, such that the etching liquid accommodated in the cleaning tank body integrally moves downwards so as to remain stationary with respect to the wafer; and a second pump, the second

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MU, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW。

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pump being used for pumping, during a process of moving the wafer out of the etching liquid accommodated in the cleaning tank body, the etching liquid at the liquid level to the bottom of the cleaning tank body via the outside of the cleaning tank body, such that the etching liquid accommodated in the cleaning tank body integrally moves upwards so as to remain stationary with respect to the wafer.

(57) 摘要: 本申请实施例公开了一种用于清洗晶圆的装置和方法, 该装置可以包括: 清洗槽体; 第一泵, 所述第一泵用于在将所述晶圆浸入容纳在所述清洗槽体中的刻蚀液的过程中, 经由所述清洗槽体外部将所述清洗槽体的底部处的刻蚀液泵送至容纳在所述清洗槽体中的刻蚀液的液面处, 以使容纳在所述清洗槽体中的刻蚀液整体上向下移动成使得相对于所述晶圆保持静止; 第二泵, 所述第二泵用于在将所述晶圆从容纳在所述清洗槽体中的刻蚀液移出的过程中, 经由所述清洗槽体外部将所述液面处的刻蚀液泵送至所述清洗槽体的底部处, 以使容纳在所述清洗槽体中的刻蚀液整体上向上移动成使得相对于所述晶圆保持静止。